

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	65	(large or big) near3 (void or hole or empty or null) same (fluorocarbon or fluoro carbon)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/09/14 00:43
L3	0	(first and second) adj3 (carbon fluoride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/09/14 00:44
L4	0	(first and second) near3 (carbon fluoride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/09/14 00:45
L5	192	(first and second) same (carbon fluoride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/09/14 00:46
L6	11	(first and second) near3 (carbon fluoride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/09/14 00:46
L7	1	L2 and L5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/09/14 00:47
L8	1	L2 and L6	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/09/14 00:47
L9	14	((carbon near3 fluorocarbon) adj3 (film or gas or layer)) near5 (substrate or wafer or semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/09/14 00:49

L10	0	L9 and L6	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/09/14 00:49
L11	0	L9 and L2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/09/14 00:49
L12	32633	(fluoride or fluor\$3 or fluorocarbon or fluoro-carbon or carbon) near5 (film or layer or dielectric or di-electric or di electric) same (void or space or hole or well)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/09/14 00:50
L13	5	L9 and L12	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/09/14 00:50
L14	28	L5 and L12	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/09/14 00:50
L15	4	L6 and L12	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/09/14 00:51
L16	1	(first and second) near3 (carbon fluoride) adj gas same (substrate or wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/09/14 00:52
L17	1	(first and second) near3 (carbon fluoride) adj5 gas same (substrate or wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/09/14 00:53
L18	1	(first and second) adj3 ((carbon fluoride) adj5 gas) same (substrate or wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/09/14 00:54

L19	28	L2 and L12	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/09/14 00:59
L20	1	L14 and L19	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/09/14 01:00
S2	0	JP10-092804A	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/01 13:16
S3	0	JP 10-092804A	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/01 13:16
S4	0	"092804".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/01 13:17
S5	1	"6524963".PN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/01 13:17
S6	1	"20070020951".PN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/01 13:23
S7	2440	(first or second or third) near3 (fluoride or fluor\$3 or fluorocarbon or fluoro-carbon or carbon) near5 (substrate or wafer or semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/01 13:39
S8	31130	(fluoride or fluor\$3 or fluorocarbon or fluoro-carbon or carbon) near5 (film or layer or dielectric or di-electric or di electric) same (void or space or hole or well)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/01 13:41
S10	2440	(first or second or third) near3 (fluoride or fluor\$3 or fluorocarbon or fluoro-carbon or carbon) near5 (substrate or wafer or semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/01 20:13

S11	31130	(fluoride or fluor\$3 or fluorocarbon or fluoro-carbon or carbon) near5 (film or layer or dielectric or di-electric or di electric) same (void or space or hole or well)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/01 20:13
S12	579	S10 and S11	US-PGPUB; USPAT; USOCR	OR	ON	2009/04/01 20:13
S13	0	((first or second or third) near3 ((carbon adj3 fluorocarbon) adj3 (film or gas or layer)) near5 (substrate or wafer or semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/01 20:16
S14	2	((first or second or third) near3 (carbon adj3 fluorocarbon) adj3 (film or gas or layer) same (substrate or wafer or semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/01 20:16
S15	29211053	@ad<"20040722" or @rlad<"20040722"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/01 20:18
S16	447	S12 and S15	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/01 20:19
S17	14	((carbon near3 fluorocarbon) adj3 (film or gas or layer)) near5 (substrate or wafer or semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/01 20:21
S18	13	S17 and S15	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/01 20:21
S19	1	((first or second or third) near3 ((carbon adj3 fluorocarbon) adj3 (film or gas or layer)) near5 (void or hole or space)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/01 20:37
S20	2	("6531409" "6419985").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/04/02 11:54

S21	11596	(remov\$3 or cut\$3 or etch\$3) near3 (volatil\$3 or explosiv\$3 or unstabl\$3) same (carbon or fluorine or fluorocarbon or fluoride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/02 11:58
S22	902	(remov\$3 or cut\$3 or etch\$3) near3 (volatil\$3 or explosiv\$3 or unstabl\$3) same (carbon or fluorine or fluorocarbon or fluoride) with (void or vacuum or space or hole or well)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/02 11:59
S23	29211485	@ad<"20040722" or @rlad<"20040722"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/02 11:59
S24	2442	(first or second or third) near3 (fluoride or fluor\$3 or fluorocarbon or fluoro-carbon or carbon) near5 (substrate or wafer or semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/02 12:01
S25	31171	(fluoride or fluor\$3 or fluorocarbon or fluoro-carbon or carbon) near5 (film or layer or dielectric or di-electric or di electric) same (void or space or hole or well)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/02 12:01
S26	579	S24 and S25	US-PGPUB; USPAT; USOCR	OR	ON	2009/04/02 12:01
S27	2	S22 and S26	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/02 12:01
S28	6	("5900290" "6005291" "6071797" "6091081" "6215087").PN. OR ("6419985").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/02 12:02
S29	2	("5525447" "6121162").PN. OR ("6531409").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/02 12:03
S30	34	("6215087").URPN.	USPAT	ADJ	ON	2009/04/02 12:08
S31	149	((((carbon adj3 fluoride) adj3 gas) or fluorocarbon adj3 film) same (induct\$3 or dielectric or di electric or di-electric)	USPAT	ADJ	ON	2009/04/02 12:15
S32	2	S22 and S31	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/02 12:15

S33	0	((carbon adj3 fluoride) adj3 gas) or fluorocarbon adj3 film) same (induct\$3 adj3 capacity)	USPAT	ADJ	ON	2009/04/02 12:18
S34	0	((carbon adj3 fluoride) adj3 gas) or fluorocarbon adj3 (film or layer)) same (induct\$3 adj3 capacity)	USPAT	ADJ	ON	2009/04/02 12:19
S35	34471	438/400-404,584-597,622-624,637,672-675,700,733,734,758-763,778-780.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/02 12:30
S36	9	("20040006249" "20040161946" "20040175501" "20050176230" "20060040507" "20060264059" "6429518" "6524963" "6593246").PN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/02 12:41
S37	108495	(induct\$3 or deduct\$3 or causat\$3 or insulat\$3 or (low\$3 adj3 (dielectric or di-electric or di electric))) near5 (constant or capacit\$3) same (less or low \$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/04 20:59
S38	29211485	@ad< "20040722" or @rlad< "20040722"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/04 21:00
S39	2442	(first or second or third) near3 (fluoride or fluor\$3 or fluorocarbon or fluoro-carbon or carbon) near5 (substrate or wafer or semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/04 21:00
S40	31171	(fluoride or fluor\$3 or fluorocarbon or fluoro-carbon or carbon) near5 (film or layer or dielectric or di-electric or di electric) same (void or space or hole or well)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/04 21:00
S41	579	S39 and S40	US-PGPUB; USPAT; USOCR	OR	ON	2009/04/04 21:00
S42	447	S41 and S38	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/04 21:01

S43	106	S37 and S42	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/04 21:01
S44	2442	(first or second or third) near3 (fluoride or fluor\$3 or fluorocarbon or fluoro-carbon or carbon) near5 (substrate or wafer or semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/04 21:02
S45	31171	(fluoride or fluor\$3 or fluorocarbon or fluoro-carbon or carbon) near5 (film or layer or dielectric or di-electric or di electric) same (void or space or hole or well)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/04 21:02
S46	579	S44 and S45	US-PGPUB; USPAT; USOCR	OR	ON	2009/04/04 21:02
S47	106	S43 and S46	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/04 21:02
S48	14	((carbon near3 fluorocarbon) adj3 (film or gas or layer)) near5 (substrate or wafer or semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/04 21:03
S49	0	S48 and S47	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/04 21:03
S50	34471	438/400-404,584-597,622- 624,637,672- 675,700,733,734,758-763,778- 780.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/04 21:04
S51	35	S50 and S47	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/04 21:04
S52	0	S51 and (((carbon near3 fluorocarbon) adj3 (film or gas or layer)) same (substrate or wafer or semiconductor))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/04 21:05

S53	0	S51 and ((carbon near3 fluorocarbon) adj3 (film or gas or layer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/04/04 21:05
-----	---	---	---	-----	----	---------------------

EAST Search History (I nterference)

< This search history is empty >

9/ 14/ 2009 1:11:23 AM

**C:\ Documents and Settings\ amustapha\ My Documents\ EAST\ Workspaces\ 10_536774 (Fluorocarbon
film and method for forming same).w sp**